### **Vishay Semiconductors**

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## Hyperfast Rectifier, 5 A FRED Pt<sup>®</sup>



TO-252AA (D-PAK)

PRODUCT SUMMARY								
Package	TO-252AA (D-PAK)							
I <sub>F(AV)</sub>	5 A							
V <sub>R</sub>	600 V							
V <sub>F</sub> at I <sub>F</sub>	1.2 V							
t <sub>rr</sub> (typ.)	18 ns							
T <sub>J</sub> max.	175 °C							
Diode variation	Single die							

### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub> and soft recovery
- 175 °C maximum operating junction temperature
- For PFC CRM/CCM operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Peak repetitive reverse voltage	V <sub>RRM</sub>		600	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 150 °C	5							
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	70	А						
Peak repetitive forward current	I <sub>FM</sub>	$T_{C} = 150 \ ^{\circ}C, f = 20 \ \text{kHz}, d = 50 \ \%$	10							
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 5 A	-	1.54	1.85	V			
		I <sub>F</sub> = 5 A, T <sub>J</sub> = 150 °C	-	1.20	1.40				
Reverse leakage current		$V_R = V_R$ rated	-	-	5				
neverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	130	μA			
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	3.5	-	pF			
Series inductance	LS	Measured lead to lead 5 mm from package body	-	8	-	nH			

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 \text{ A}, dI_F/dt = 10$	00 A/µs, V <sub>R</sub> = 30 V	-	18	25				
	+	$I_F = 1 \text{ A}, dI_F/dt = 50$	-	22	-	ns				
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	25	-	115			
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 5 A dI <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 390 V	-	35	-				
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	3.9	-	А			
Peak recovery current		T <sub>J</sub> = 125 °C		-	5.1	-	~			
Deverse we can all and	0	T <sub>J</sub> = 25 °C		-	51	-	nC			
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		_	93	-				

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C			
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	-	3	°C/W			
Approximate weight				0.3		g			
Approximate weight				0.01		oz.			
Marking device		Case style TO-252AA (D-PAK)	5EWH06FN						

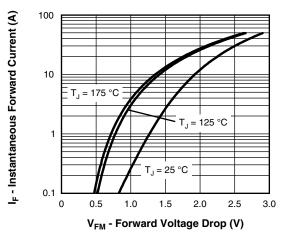
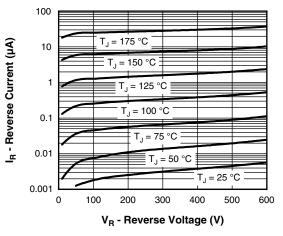
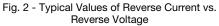


Fig. 1 - Typical Forward Voltage Drop Characteristics





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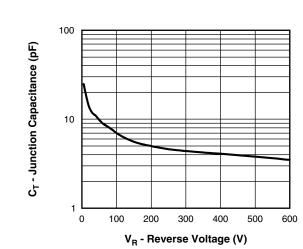


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

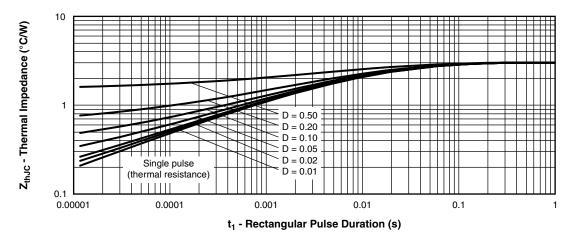
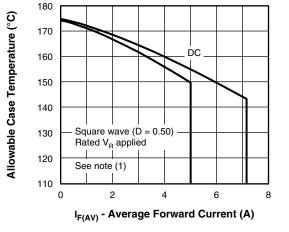


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

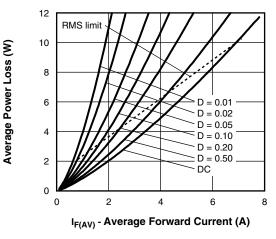


Fig. 6 - Forward Power Loss Characteristics

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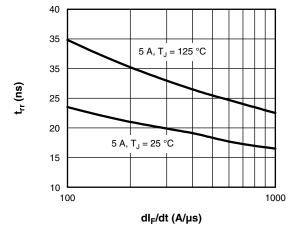


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

#### Note

- $\begin{array}{ll} \mbox{(1)} & \mbox{Formula used: } T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \mbox{forward power loss} = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6); } \\ Pd_{REV} = \mbox{inverse power loss} = V_{R1} \times I_R \mbox{ (1 D); } I_R \mbox{ at } V_{R1} = \mbox{rated } V_R \mbox{ at } V_{R1} = \mbox{rated } V_R \mbox{ at } V_{R1} \mbox{ at } V_$

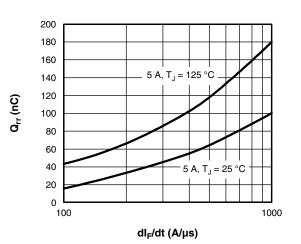


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

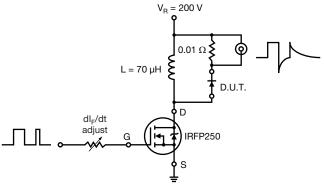


Fig. 9 - Reverse Recovery Parameter Test Circuit

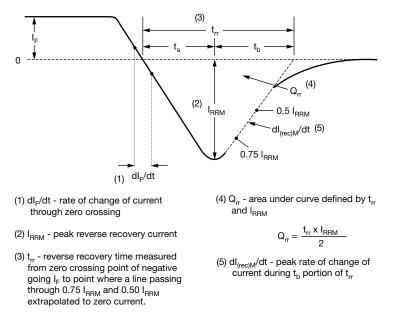


Fig. 10 - Reverse Recovery Waveform and Definitions



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**ORDERING INFORMATION TABLE** 

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									-
Device code	VS-	5	Е	w	н	06	FN	TRL	-M3
	1	2	3	4	5	6	7	8	9
	1 · · · · · · · · · · · · · · · · · · ·	- Cur - Circ E = - Pac	rent rati cuit conf single c ckage ide	entifier:	5 A)	oduct			
	7	<ul> <li>6 - Voltage rating (06 = 600 V)</li> <li>7 - FN = TO-252AA</li> </ul>							
	9.	• TI • TI • Env	RL = tap RR = tap rironmer	e and report of and report of and report of and report of and report of and report of a set of a set o	eel (left eel (righ :	nt orient	ed)	tormino	4: I

-M3 = halogen-free, RoHS-compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-5EWH06FN-M3	75	3000	Antistatic plastic tube							
VS-5EWH06FNTR-M3	2000	2000	13" diameter reel							
VS-5EWH06FNTRL-M3	3000	3000	13" diameter reel							
VS-5EWH06FNTRR-M3	3000	3000	13" diameter reel							

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95627							
Part marking information	www.vishay.com/doc?95176							
Packaging information	www.vishay.com/doc?95033							
SPICE model	www.vishay.com/doc?95186							





D-PAK (TO-252AA) "M"

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51	BSC	0.020	BSC	
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension uncontrolled in L5

<sup>(3)</sup> Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(6)</sup> Dimension b1 and c1 applied to base metal only

<sup>(7)</sup> Datum A and B to be determined at datum plane H

<sup>(8)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-252AA



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